

# Super-Resolution by Nonlinear Optical Lithography



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# Outline



- **Resolution Issues in Lithography**
- **Review of Previous Proposals**
- **Classical Multi-Photon Lithography**
- **Experimental Results**
- **Conclusions and Future Work**

# Lithography & the Rayleigh Limit

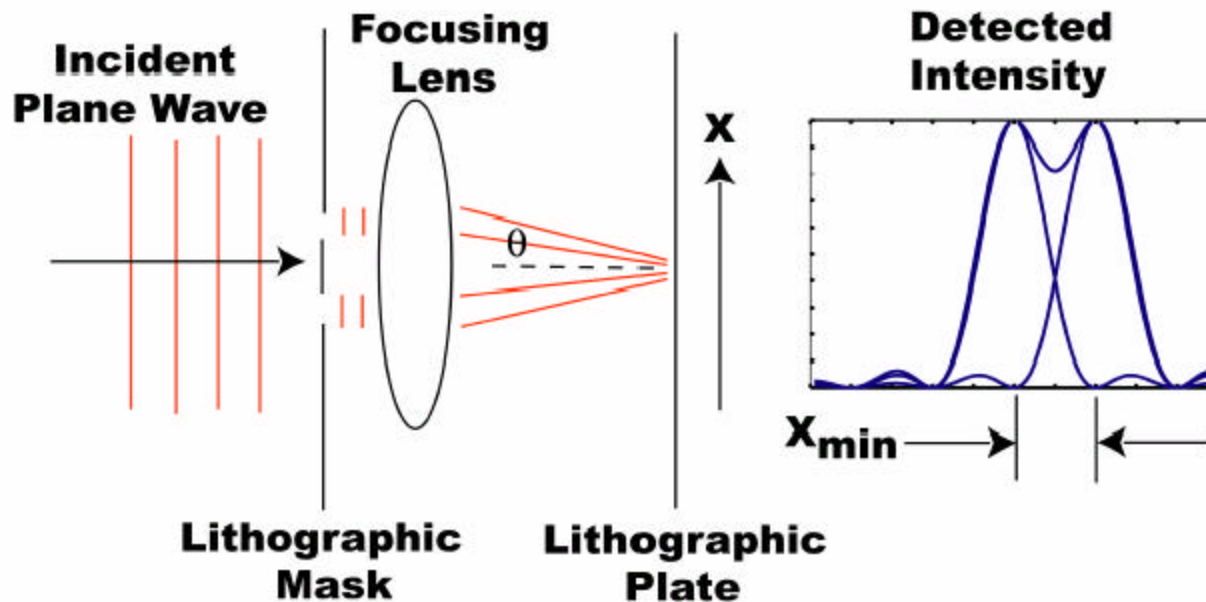
In common lithographic terminology, the Rayleigh limit is generalized to:

$$X_{min} = \lambda k_1 / NA$$

where  $k_1$  is a parameter measuring degree of imaging (0.5 for original Rayleigh peak-to-valley with rectangular aperture). Number of **writeable elements** on a surface increases **quadratically** with decreasing  $X_{min}$ , so important to minimize. Here will assume **wavelength and numerical aperture fixed**, and focus on methods to **minimize  $k_1$** .

# Mask Lithography

Traditional Optical Mask Lithography is Limited By Diffraction

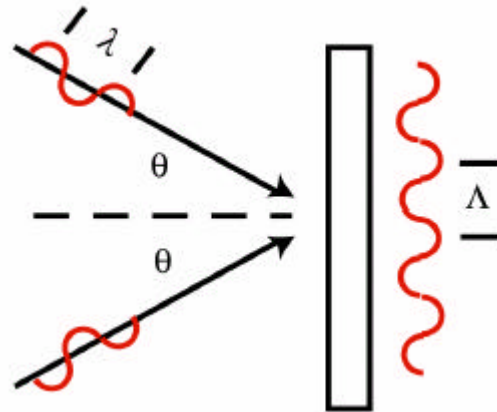


Numerical Aperture:  $NA = \sin(q)$

Minimum Resolvable Feature Size Based on Diffraction is  $X_{min} = 1/NA$   
(Rayleigh Limit)

# Interferometric Lithography

Classical Interferometric Lithography (CIL) is Limited by the Fringe Spacing



$$R_{min} = \Lambda/2 = \lambda/4 \sin \theta$$

Minimum Resolvable Feature At Grazing Incidence is  $R_{min} = \lambda/4$   
(Modified Rayleigh Limit For Classical Lithography)

S.R.J. Brueck, et al., *Microelectron. Eng.* 42, 145 (1998).

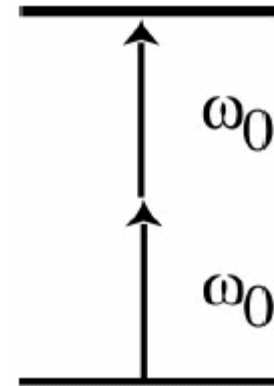
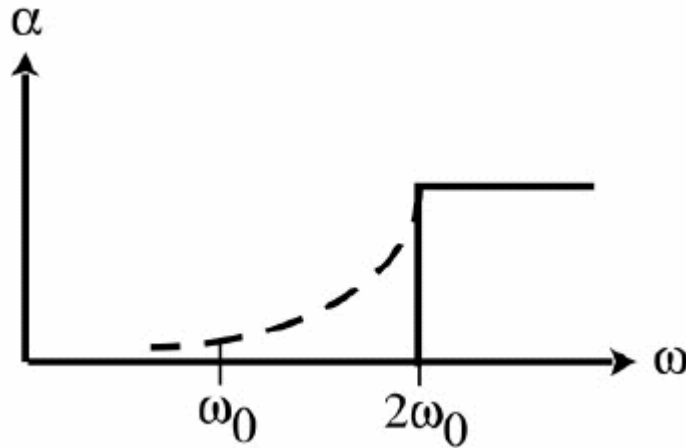
# Previous Proposals for Increased Resolution

Both **classical** (eg, E. Yablonovitch and R.B. Vrijen, Opt. Eng. 38, 334 (1999)) and **quantum** (eg, A.N. Boto, P. Kok, D.S. Abrams, S.L. Braunstein, C.P. Williams, and J.P. Dowling, Phys. Rev. Lett. 85, 2773 (2000)) optical techniques have been proposed, relying on **multi-photon absorption**.

# Previous Proposals for Increased Resolution

- Essentially all existing proposals are **interferometric** techniques
- Quantum techniques have disadvantage of **low deposition rate**
- Classical techniques have disadvantage of **low feature visibility**
- Quantum theory proposed for arbitrary resolution improvement, but beyond 2x experimental technique not yet realized
- Classical techniques only proposed for 2x improvement

# Two-Photon Absorption

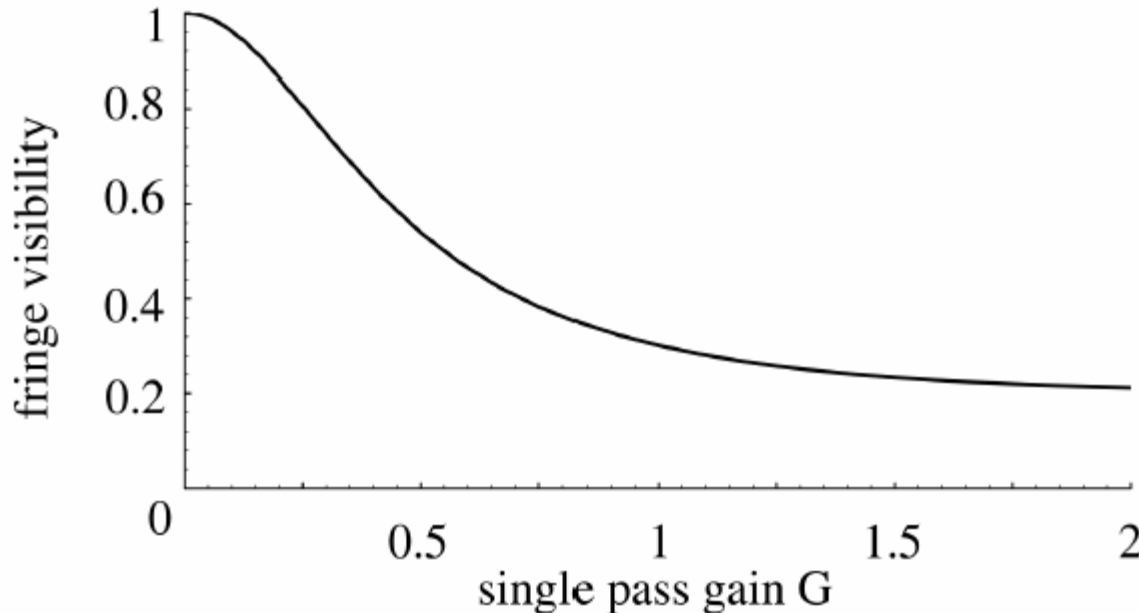


Two-photon absorption generally requires **high intensities** since the absorption cross-section scales with the intensity squared rather than linearly in the intensity as is the case for linear absorption.



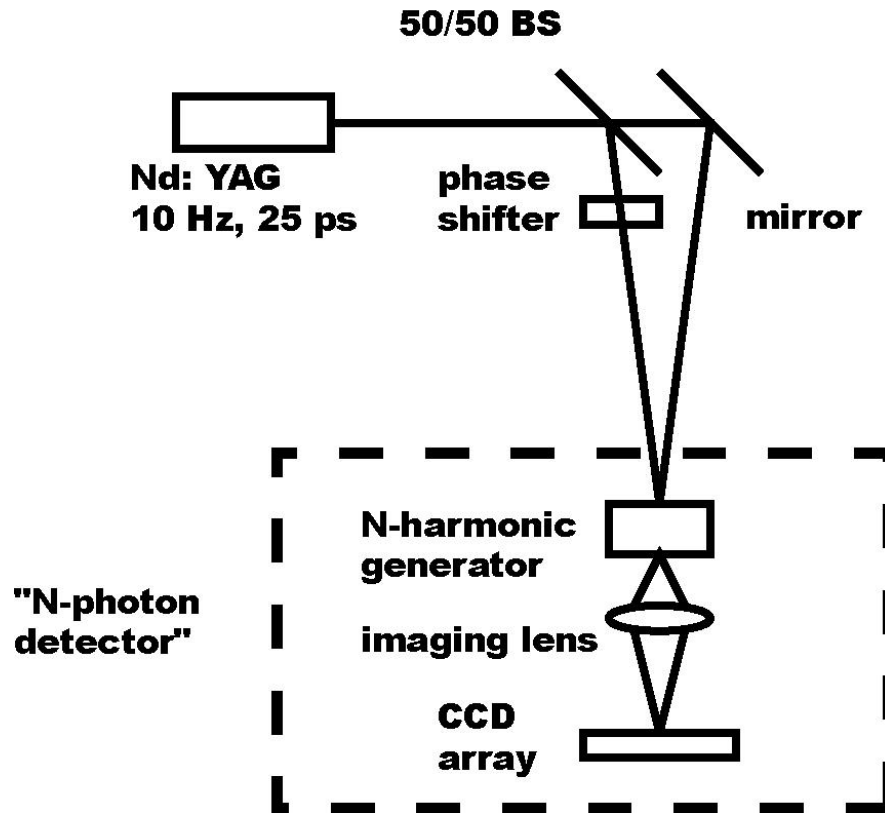
# High-Gain Quantum Lithography Theory

As the gain is increased (the pump is turned up) for the amplifier, the **fringe visibility** does decrease, but **never below 20%**.



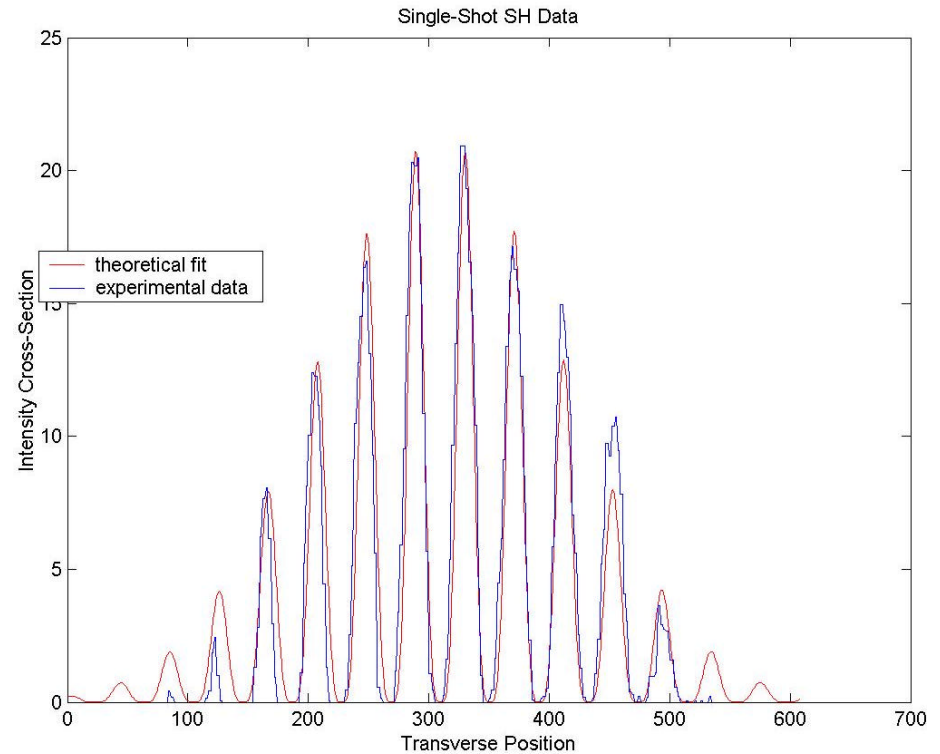
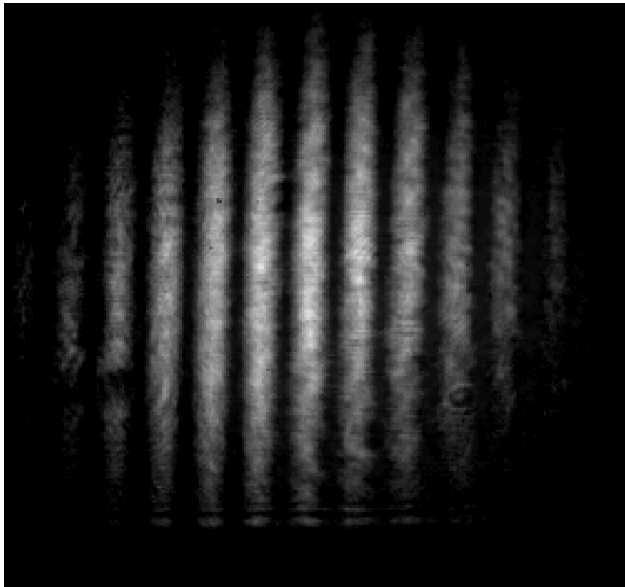
G.S. Agarwal, R.W. Boyd, E.M. Nagasako, and S.J. Bentley, Phys. Rev. Lett. 86, 1389 (2001).

# Interferometric Experimental Schematic

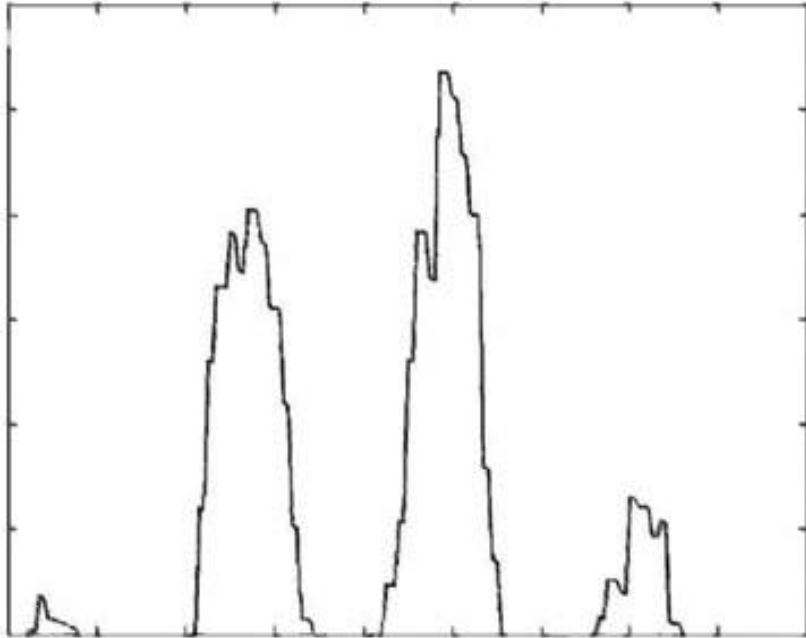


Write pattern with N-shots varying phase by  $2\pi/N$  for each successive shot.

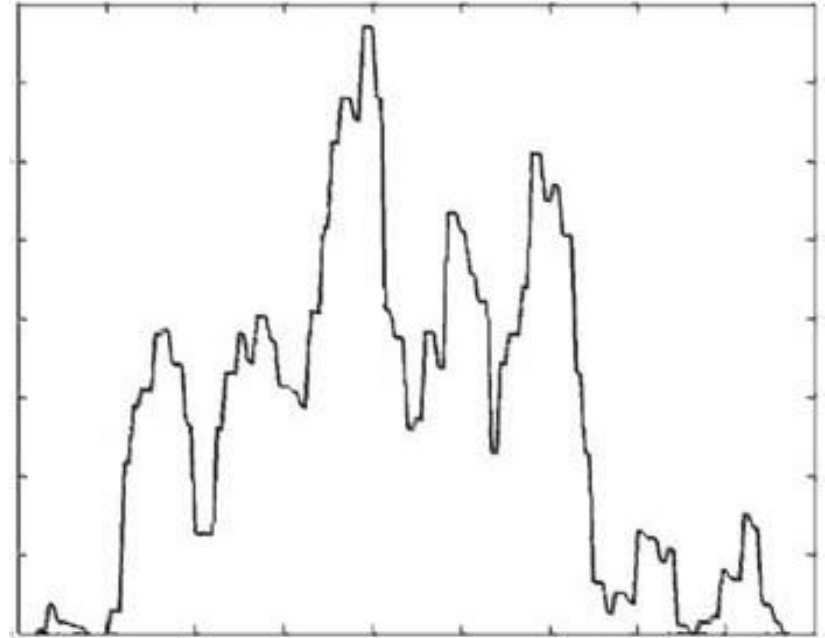
# Nonlinear Interferometric Lithography Data



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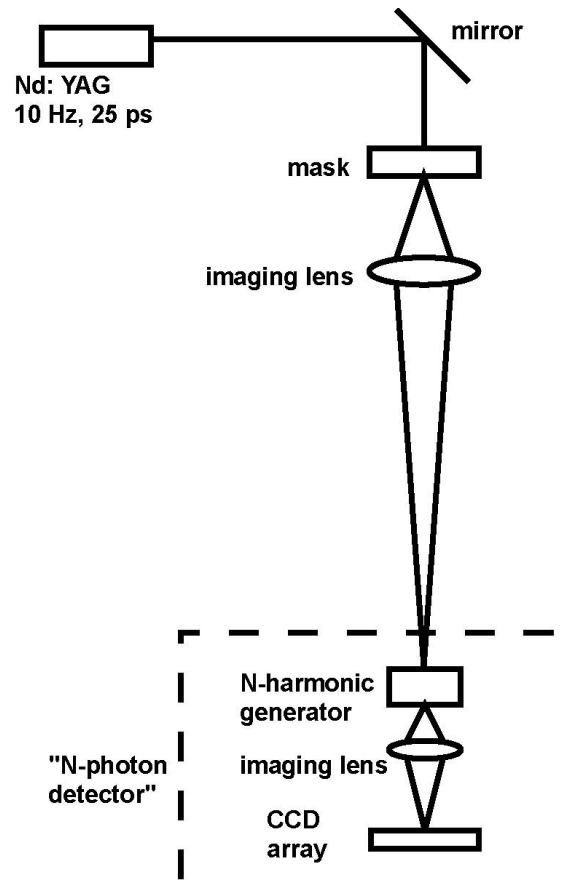


**Single-Shot Interference  
Intensity Cross-Section**

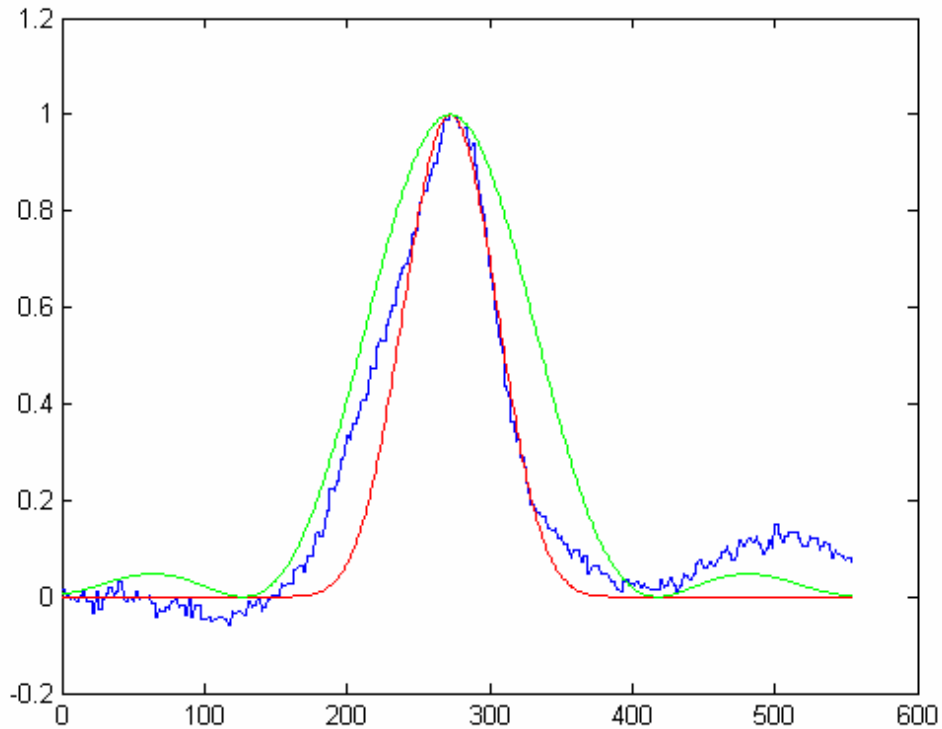


**Summed, p-Phased Interference  
Intensity Cross-Section**

# Mask Experimental Schematic



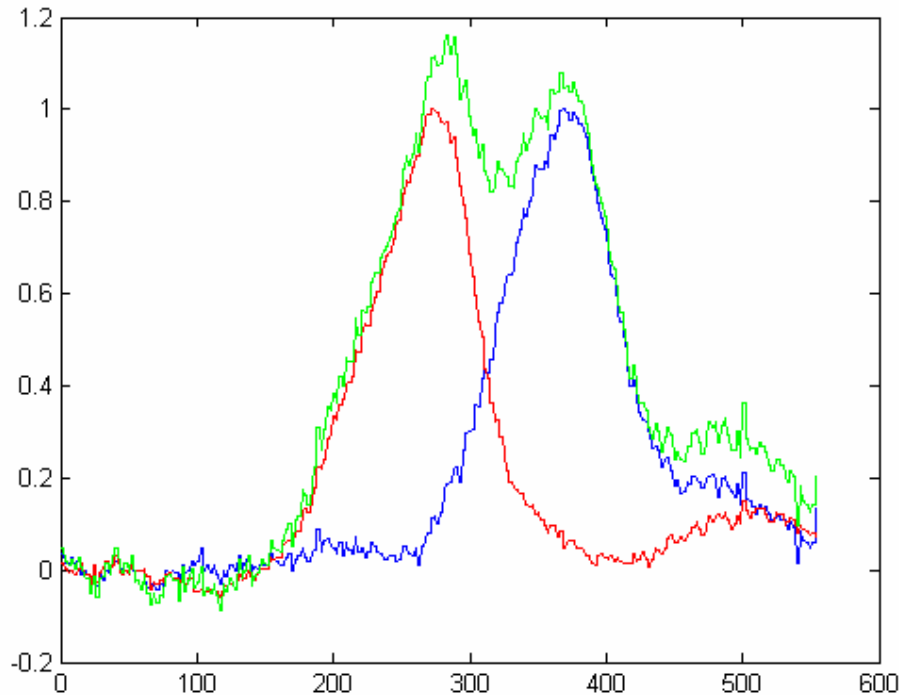
# Nonlinear Mask Lithography Data



**Blue: Data**  
**Red: Sinc<sup>6</sup> (desired)**  
**Green: Sinc<sup>2</sup>**

**Single-Shot Mask Pattern Showing Near-Desired Shape**

# Nonlinear Mask Lithography Data



**Blue: Pulse 1**

**Red: Pulse 2 (shifted 991 μm)**

**Green: Sum**

**For 1-Photon case, need  
shift of ~1716 μm for same  
visibility**

**Two-Shot Mask Data Showing  $\sim x3^{0.5}$  Improved Resolution**

# Conclusions



- **Proposed techniques for improving resolution by arbitrary amount**
- **Demonstrated mask technique for 2- and 3-photon cases with no loss of visibility!**
- **Demonstrated interferometric technique for 2-photon case**
- **Technique is in principal simple to extend to any level**
- **Limitations are visibility (interferometric only) and available substrate materials**



# Future Work



- **Demonstrate the technique to further levels of improvement**
- **Find practical substrate materials to go from proof-of-principal to “real” lithography**
- **Search for methods to improve visibility possible in interferometric case**
- **Write patterns using interferometric techniques**

# Acknowledgments



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